HAMAMATSU

HIGH-POWER INFRARED PULSED LASER DIODE L7060-02

FEATURES

- High output power ($\phi e p \ge 30W$)
- •High speed rise time (tr=0.5 ns typ.)

■ APPLICATIONS

- Laser rader
- Range finder
- Excitation light source
- Optical trigger
- Security barrier

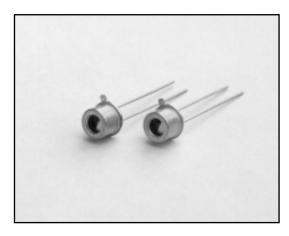
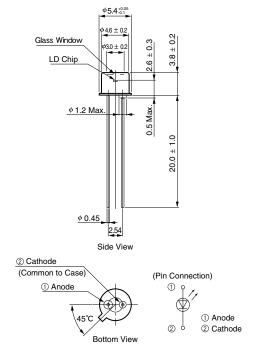


Figure 1: Dimensional Outline (Unit: mm)



■ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Pulsed Foward Current	İFP	35	Α
Reverse Voltage	VR	2	V
Pulsed Radiant Output Power	φep	40	W
Pulse Duration (FWHM)	tw	100	ns
Duty Ratio	DR	0.075	%
Operating Temperature	Тор	-30 to +85	°C
Storage Temperature	Tstg	-40 to +125	°C

■ELECTRICAL AND OPTICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Pulsed Radiant Power	ϕ ep	IFP=30A	30	-	-	W
Peak Emission Wavelength	λp		-	870	-	nm
Spectral Radiation Half Bandwidth	Δλ		-	4	-	nm
Forward Voltage	VF	IFP=30A	-	7	-	V
Rise Time	tr		-	0.5	-	ns
Beam Spread Angle : Parallel	θ//	FWHM	-	9	-	degree
: Vertical	$\theta \perp$	IFP=30A	-	30	-	degree
Lasing Threshold Current	lth		-	1	-	A

Note: General operating condition $\phi_{ep} \leq 30$ W, tw ≤ 50 ns, Repetition frequency ≤ 8 kHz

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